

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended): A method of fabricating a semiconductor device, the method comprising:

forming a gate on a semiconductor substrate, the gate including opposing side surfaces and a top surface;

after forming the gate, selectively depositing an oxide material comprising at least one material from ~~of~~ the group consisting of AlO_3 , ZrO_2 , HfO_2 (AlHf) O_x , HfO_2 , ~~La_2O_3~~ La_2O_3 , Y_2O_3 , silicon oxynitride, and hafnium silicon oxynitride substantially on the top surface of the gate, as well as over the semiconductor substrate, the opposing side surfaces of the gate being substantially free of the oxide material; and

forming spacers on the opposing side surfaces of the gate subsequent to depositing said oxide material, the spacers contacting the opposing side surfaces of the gate substantially along the opposing side surfaces.

Claim 2 (original): The method of claim 1, the gate being doped with p-type or n-type dopant.

Claim 3 (canceled)

Claim 4 (previously presented): The method of claim 1 wherein the oxide material is deposited by physical vapor deposition.

Claim 5 (canceled)

Claim 6: (original): The method of claim 4, the physical vapor deposition method comprising at least one of a collimated sputtering method, a long throw sputtering method, or an ionized metal plasma sputtering method.

Claim 7 (canceled)

Claim 8 (original): The method of claim 1, the formation of the spacers further comprising providing a nitride layer over the gate after depositing the oxide material; and etching the nitride layer.

Claim 9 (original): The method of claim 8, further comprising implanting an LDD implant after forming the gate, but before depositing the oxide layer; and implanting a source/drain implant after forming the nitride spacers.

Claim 10 (original): The method of claim 9, the LDD implant and the source/drain implant forming a source region and a drain region of the semiconductor device.

Claim 11 (original): The method of claim 10, the gate forming part of a p-type metal oxide semiconductor (PMOS) structure.

Claim 12 (currently amended): A method of fabricating a semiconductor device, the method comprising:

forming a doped gate have a top surface and opposing side surfaces on a semiconductor substrate;

after forming the gate, selectively depositing an oxide material comprising at least one material from the group consisting of AlO_3 , ZrO_2 , HfO_2 (AlHf) O_x , HfO_2 , La_2O_3 , La_2O_3 , Y_2O_3 , silicon oxynitride, and hafnium silicon oxynitride substantially on the top surface of the doped gate, as well as over the semiconductor substrate, the opposing side surfaces of the gate being substantially free of the oxide material;

forming a nitride layer over the gate and the oxide material; and

etching the nitride layer to form nitride spacers on the opposing side surfaces of the gate, the nitride spacers contacting the opposing side surfaces of the gate substantially along the opposing side surfaces.

Claim 13 (original): The method of claim 12, the nitride spacers mitigating diffusion of dopants from the opposing side surfaces of the gate.

Claim 14 (original): The method of claim 12, the oxide material being deposited by physical vapor deposition.

Claim 15 (original): The method of claim 14, the physical vapor deposition method comprising at least one of a collimated sputtering method, a long throw sputtering method, or an ionized metal plasma sputtering method.

Claims 16-17 (canceled)

Claim 18 (previously presented): The method of claim 12, further comprising: implanting a LDD implant after forming the gate, but before depositing the oxide layer; and implanting a source/drain implant after forming the nitride spacers.

Claim 19 (currently amended): The method of claim 12, the gate forming part of a semiconductor device comprising a PMOS structure.

Claims 20-23 (canceled)

Claim 24 (previously presented): The method of claim 1 wherein depositing an oxide material over the gate, as well as over the semiconductor substrate and on a side of the gate, includes depositing an oxide material on the gate and on the semiconductor substrate.

Claim 25 (previously presented): The method of claim 1 wherein forming a gate on a semiconductor substrate includes forming a conductive layer over the substrate, and patterning the conductive layer to form the gate.

Claims 26-27 (canceled)